



N-Channel Depletion-Mode MOSFET

Ordering Information

BV _{DSX} / BV _{DGX}	R _{DS(ON)} (max)	I _{DSS} (min)	Order Number / Package
			TO-236AB*
500V	1.0KΩ	1.0mA	LND250K1

Product marking for SOT-23: <div style="border: 1px solid black; padding: 2px; display: inline-block;">NDE*</div> where * = 2-week alpha date code
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*Same as SOT-23. All units shipped on 3,000 piece carrier tape reels.

Features

- ESD gate protection
- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- Excellent thermal stability
- Integral source-drain diode
- High input impedance and low C_{ISS}

Applications

- Solid state relays
- Normally-on switches
- Converters
- Power supply circuits
- Constant current sources
- Input protection circuits

Absolute Maximum Ratings

Drain-to-Source Voltage	BV _{DSX}
Drain-to-Gate Voltage	BV _{DGX}
Gate-to-Source Voltage	±20V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

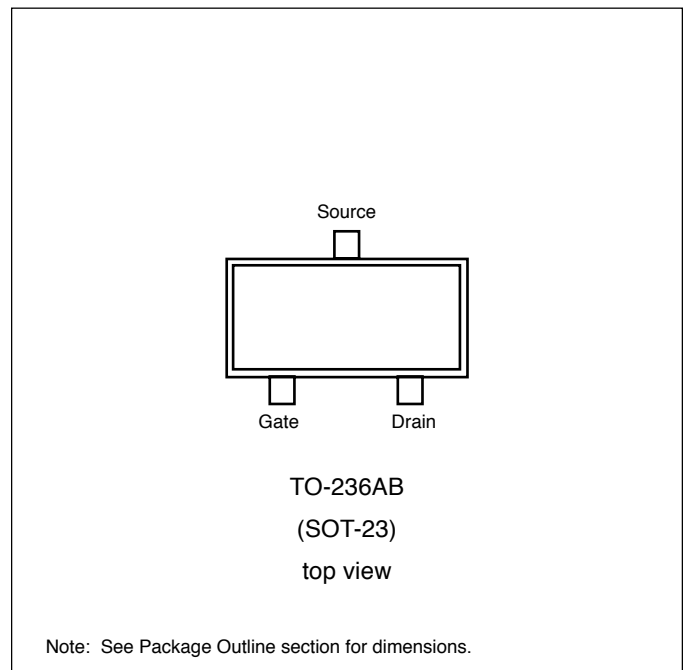
* Distance of 1.6 mm from case for 10 seconds.

Advanced DMOS Technology

The LND2 is a high voltage N-channel depletion mode (normally-on) transistor utilizing Supertex's lateral DMOS technology. The gate is ESD protected.

The LND2 is ideal for high voltage applications in the areas of normally-on switches, precision constant current sources, voltage ramp generation and amplification.

Package Options



Thermal Characteristics

Package	I_D (continuous)*	I_D (pulsed)	Power Dissipation @ $T_A = 25^\circ\text{C}$	θ_{jc} $^\circ\text{C/W}$	θ_{ja} $^\circ\text{C/W}$	I_{DR}	I_{DRM}^*
TO-236AB	13mA	30mA	0.36W	200	350	13mA	30mA

* I_D (continuous) is limited by max rated T_J .

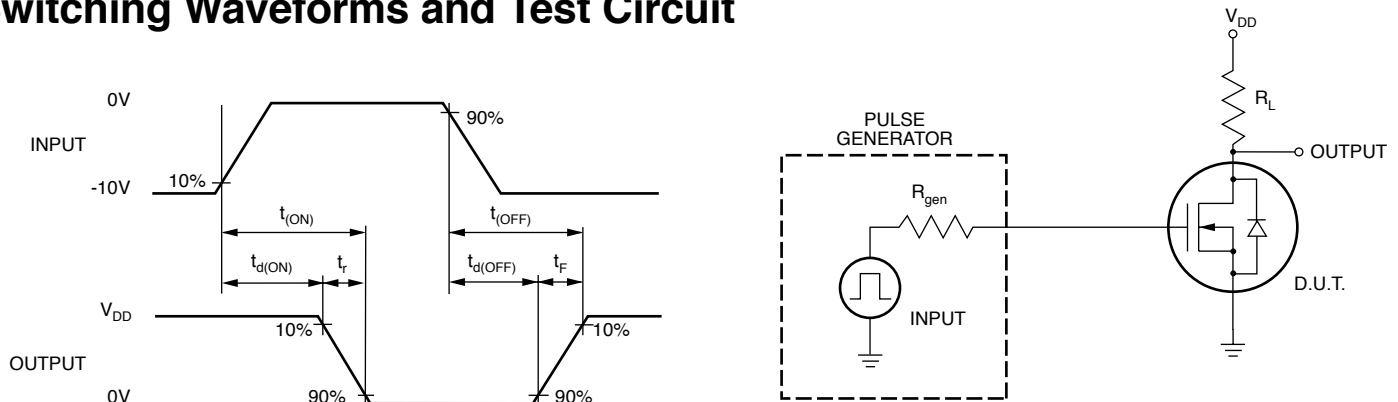
Electrical Characteristics (@ 25°C unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Unit	Conditions
BV_{DSX}	Drain-to-Source Breakdown Voltage	500			V	$V_{GS} = -10\text{V}$, $I_D = 1.0\text{mA}$
$V_{GS(OFF)}$	Gate-to-Source OFF Voltage	-1.0		-3.0	V	$V_{DS} = 25\text{V}$, $I_D = 100\text{nA}$
$\Delta V_{GS(OFF)}$	Change in $V_{GS(OFF)}$ with Temperature			5.0	mV/ $^\circ\text{C}$	$V_{DS} = 25\text{V}$, $I_D = 100\text{nA}$
I_{GSS}	Gate Body Leakage Current			100	nA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$
$I_{D(OFF)}$	Drain-to-Source Leakage Current			100	nA	$V_{GS} = -10\text{V}$, $V_{DS} = 450\text{V}$
				100	μA	$V_{GS} = -10\text{V}$, $V_{DS} = 0.8\text{V}$ max rating $T_A = 125^\circ\text{C}$
I_{DSS}	Saturated Drain-to-Source Current	1.0		3.0	mA	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$
$R_{DS(ON)}$	Static Drain-to-Source ON-State Resistance		850	1K	Ω	$V_{GS} = 0\text{V}$, $I_D = 0.5\text{mA}$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with Temperature			1.2	%/ $^\circ\text{C}$	$V_{GS} = 0\text{V}$, $I_D = 0.5\text{mA}$
G_{FS}	Forward Transconductance	1.0	2.0		m \bar{S}	$V_{GS} = 0\text{V}$, $I_D = 1.0\text{mA}$
C_{ISS}	Input Capacitance		7.5	10	pF	$V_{GS} = -10\text{V}$, $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$
C_{OSS}	Output Capacitance		2.0	3.5		
C_{RSS}	Reverse Transfer Capacitance		0.5	1.0		
$t_{d(ON)}$	Turn-ON Delay Time		0.09		μs	$V_{DD} = 25\text{V}$, $I_D = 1.0\text{mA}$, $R_{GEN} = 25\Omega$
t_r	Rise Time		0.45			
$t_{d(OFF)}$	Turn-OFF Delay Time		0.1			
t_f	Fall Time		1.3			
V_{SD}	Diode Forward Voltage Drop			0.9	V	$V_{GS} = -10\text{V}$, $I_{SD} = 1.0\text{mA}$
t_{rr}	Reverse Recovery Time		200		ns	$V_{GS} = -10\text{V}$, $I_{SD} = 1.0\text{mA}$

Notes:

- All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: $300\mu\text{s}$ pulse, 2% duty cycle.)
- All A.C. parameters sample tested.

Switching Waveforms and Test Circuit



12/13/010